

IN THE CLAIMS:

Please cancel Claims 7 and 14 without prejudice.

Please amend Claims 1, 8, and 9 by rewriting the same as follows:

sub D1
B19
1. (Amended) A damascene interconnection comprising:
an interconnection trench formed in an insulating film and a pad trench
communicating therewith;
a protrusion formed by a portion not removed of said insulating film in said
pad trench to decrease a substantial opening area of said pad trench;
a conductive film buried in said interconnection trench and said pad trench;
and
a contact hole formed within said pad trench to electrically connect said
conductive film to a further conductive film formed below said insulating film, wherein said
contact hole and said further conductive film substantially suppress an increase in electrical
resistance in said pad trench due to formation of said protrusion.

sub D2 cont
B20
8. (Amended) A semiconductor device, comprising:
a semiconductor substrate;
an insulating film formed on said semiconductor substrate;
an interconnection trench formed on said insulating film and communicating
with a semiconductor element;
a pad trench formed on said insulating film and communicating with said
interconnection trench;
a protrusion formed by a portion of not removed of said insulating film in said
pad trench and reducing a substantial opening area of said pad trench;
a conductive film buried in said interconnection trench and said pad trench;
a further conductive film formed below said insulating film; and